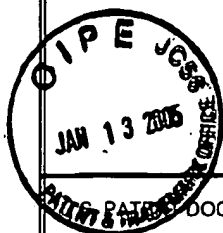


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## PATENT DOCUMENTS

*Examiner's Initials		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
	AA						
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	AD						
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	AH						
	AI						

## FOREIGN PATENT DOCUMENTS

		Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
	AJ							
	AK							
	AL							

## OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)

EF	AM		S.M. George, "Atomic layer controlled deposition of SiO <sub>2</sub> and Al <sub>2</sub> O <sub>3</sub> using ABAB...binary reaction sequence chemistry", <i>Elsevier Science B.V., Applied Surface Science</i> 82/83, 1994, p. 460-467.
	AN		
	AO		

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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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EF	AA	6,495,436	12/17/2002	Ahn et al.			
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		Document Number	Date	Country	Class	Subclass	Translation	
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EF	AR		"Surface preparation and post thermal treatment effects on interface properties of thin Al <sub>2</sub> O <sub>3</sub> films deposited by ALD;" Chang et al.; Microelectronic Engineering 72, 2004; pp. 326-331.					
EF	AS		"Effect Purge time on the properties of HfO <sub>2</sub> films prepared by atomic layer deposition;" Kawahara et al.; IEEE Transactions on Electronics; Vol. E87-C, No. 1; January 2004; pp. 2-8.					
EF	AT		"High-k materials for advanced gate stack dielectrics: a comparison of ALGVD and MOCVD as deposition technologies;" Caymax et al.; CMOS Front-End materials and Process Technology Symposium (Mater. Res. Soc. Symposium Proceedings Vol. 765); April 22-24, 2003; 47-58					

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							Yes	No
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EF	AR		"Effect of HF sources, oxidizing agents, and NH <sub>3</sub> /Ar plasma on the properties of HfAlO <sub>3</sub> films prepared by atomic layer deposition;" Kawahara et al.; Japanese Journal of Applied Physics, Vol. 43, No. 7A; July 2004; pp. 4129-4134.
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